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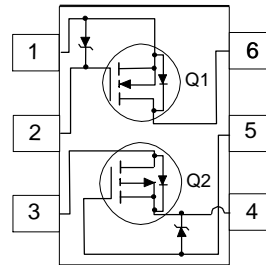
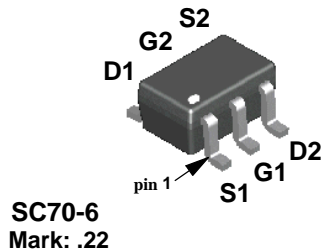
## FDG6322C Dual N & P Channel Digital FET

### General Description

These dual N & P-Channel logic level enhancement mode field effect transistors are produced using ON Semiconductor's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. This device has been designed especially for low voltage applications as a replacement for bipolar digital transistors and small signal MOSFETs. Since bias resistors are not required, this dual digital FET can replace several different digital transistors, with different bias resistor values.

### Features

- N-Ch 0.22 A, 25 V,  $R_{DS(ON)} = 4.0 \Omega @ V_{GS} = 4.5 \text{ V}$ ,  
 $R_{DS(ON)} = 5.0 \Omega @ V_{GS} = 2.7 \text{ V}$ .
- P-Ch -0.41 A, -25V,  $R_{DS(ON)} = 1.1 \Omega @ V_{GS} = -4.5 \text{ V}$ ,  
 $R_{DS(ON)} = 1.5 \Omega @ V_{GS} = -2.7 \text{ V}$ .
- Very small package outline SC70-6.
- Very low level gate drive requirements allowing direct operation in 3 V circuits ( $V_{GS(th)} < 1.5 \text{ V}$ ).
- Gate-Source Zener for ESD ruggedness (>6kV Human Body Model).



### Absolute Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	N-Channel	P-Channel	Units
$V_{DSS}$	Drain-Source Voltage	25	-25	V
$V_{GSS}$	Gate-Source Voltage	8	-8	V
$I_D$	Drain Current - Continuous	0.22	-0.41	A
	- Pulsed	0.65	-1.2	
$P_D$	Maximum Power Dissipation (Note 1)	0.3		W
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to 150		$^\circ\text{C}$
ESD	Electrostatic Discharge Rating MIL-STD-883D Human Body Model (100pf / 1500 Ohm)	6		kV

### THERMAL CHARACTERISTICS

$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note1)	415	$^\circ\text{C/W}$
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**DMOS Electrical Characteristics** ( $T_A = 25\text{ }^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Type	Min	Typ	Max	Units
<b>OFF CHARACTERISTICS</b>							
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	N-Ch	25			V
		$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-25			
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	$I_D = 250\text{ }\mu\text{A}$ , Referenced to $25\text{ }^\circ\text{C}$	N-Ch		25		mV/°C
		$I_D = -250\text{ }\mu\text{A}$ , Referenced to $25\text{ }^\circ\text{C}$	P-Ch		-22		
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$ , $T_J = 55\text{ }^\circ\text{C}$	N-Ch			1 10	$\mu\text{A}$
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$ , $T_J = 55\text{ }^\circ\text{C}$	P-Ch			-1 -10	
$I_{GSS}$	Gate - Body Leakage Current	$V_{GS} = 8\text{ V}, V_{DS} = 0\text{ V}$	N-Ch			100	nA
		$V_{GS} = -8\text{ V}, V_{DS} = 0\text{ V}$	P-Ch			-100	nA
<b>ON CHARACTERISTICS</b> (Note 2)							
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	N-Ch	0.65	0.85	1.5	V
		$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	P-Ch	-0.65	-0.82	-1.5	
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Temp. Coefficient	$I_D = 250\text{ }\mu\text{A}$ , Referenced to $25\text{ }^\circ\text{C}$	N-Ch		-2.1		mV/°C
		$I_D = -250\text{ }\mu\text{A}$ , Referenced to $25\text{ }^\circ\text{C}$	P-Ch		2.1		
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 4.5\text{ V}, I_D = 0.22\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$	N-Ch		2.6	4	$\Omega$
		$V_{GS} = 2.7\text{ V}, I_D = 0.19\text{ A}$			5.3	7	
		$V_{GS} = -4.5\text{ V}, I_D = -0.41\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$		P-Ch		0.85	
		$V_{GS} = -2.7\text{ V}, I_D = -0.25\text{ A}$			1.2	1.9	
					1.15	1.5	
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 4.5\text{ V}, V_{DS} = 5\text{ V}$	N-Ch	0.22			A
		$V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	P-Ch	-0.41			
$g_{FS}$	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 0.22\text{ A}$	N-Ch		0.2		S
		$V_{DS} = -5\text{ V}, I_D = -0.5\text{ A}$	P-Ch		0.9		
<b>DYNAMIC CHARACTERISTICS</b>							
$C_{iss}$	Input Capacitance	N-Channel $V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}$	N-Ch		9.5		pF
			P-Ch		62		
$C_{oss}$	Output Capacitance	f = 1.0 MHz P-Channel	N-Ch		6		
			P-Ch		34		
$C_{rss}$	Reverse Transfer Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}$ , f = 1.0 MHz	N-Ch		1.3		
			P-Ch		10		

## Electrical Characteristics (continued)

### SWITCHING CHARACTERISTICS (Note 2)

Symbol	Parameter	Conditions	Type	Min	Typ	Max	Units
$t_{D(on)}$	Turn - On Delay Time	N-Channel $V_{DD} = 5\text{ V}, I_D = 0.5\text{ A},$	N-Ch		5	10	nS
			P-Ch		7	15	
$t_r$	Turn - On Rise Time	$V_{GS} = 4.5\text{ V}, R_{GEN} = 50\ \Omega$	N-Ch		4.5	10	nS
			P-Ch		8	16	
$t_{D(off)}$	Turn - Off Delay Time	P-Channel $V_{DD} = -5\text{ V}, I_D = -0.5\text{ A},$	N-Ch		4	8	nS
			P-Ch		55	80	
$t_f$	Turn - Off Fall Time	$V_{GS} = -4.5\text{ V}, R_{GEN} = 50\ \Omega$	N-Ch		3.2	7	nS
			P-Ch		35	60	
$Q_g$	Total Gate Charge	N-Channel $V_{DS} = 5\text{ V}, I_D = 0.22\text{ A},$	N-Ch		0.29	0.4	nC
			P-Ch		1.1	1.5	
$Q_{gs}$	Gate-Source Charge	$V_{GS} = 4.5\text{ V}$	N-Ch		0.12		nC
			P-Ch		0.31		
$Q_{gd}$	Gate-Drain Charge	P-Channel $V_{DS} = -5\text{ V}, I_D = -0.41\text{ A},$ $V_{GS} = -4.5\text{ V}$	N-Ch		0.03		nC
			P-Ch		0.29		

### DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

$I_S$	Maximum Continuous Drain-Source Diode Forward Current		N-Ch			0.25	A
			P-Ch			-0.25	
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 0.5\text{ A}$ (Note 2)	N-Ch		0.8	1.2	V
		$V_{GS} = 0\text{ V}, I_S = -0.5\text{ A}$ (Note 2)	P-Ch		-0.85	-1.2	

Notes:

- $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.  $R_{\theta JA} = 415^\circ\text{C/W}$  on minimum mounting pad on FR-4 board in still air.
- Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

## Typical Electrical Characteristics: N-Channel

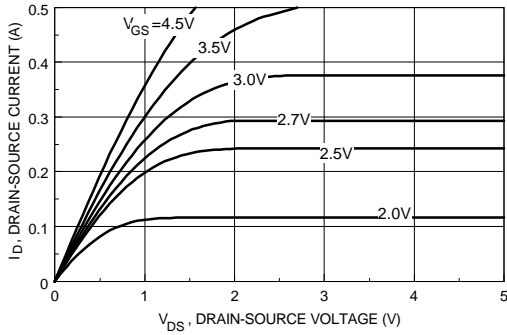


Figure 1. On-Region Characteristics.

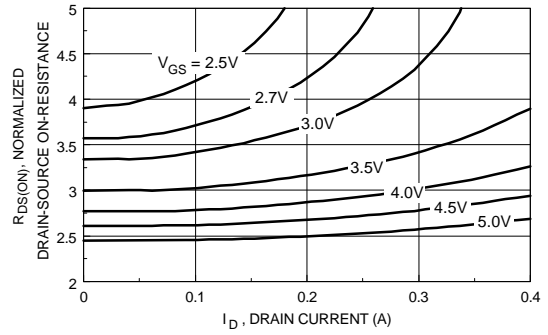


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

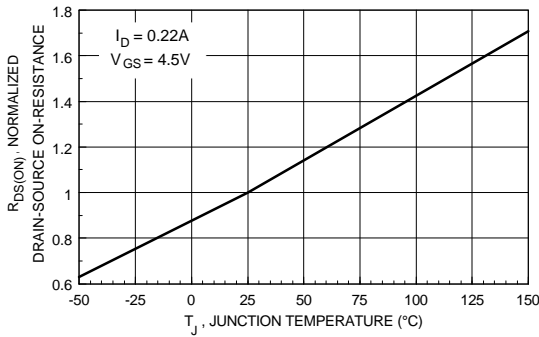


Figure 3. On-Resistance Variation with Temperature.

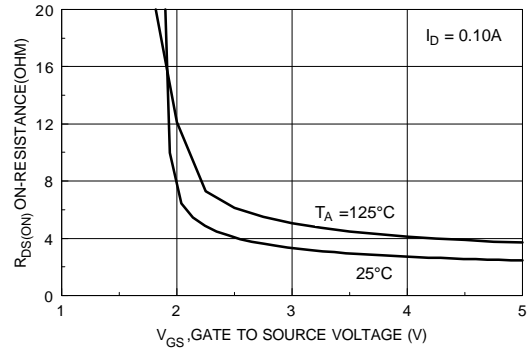


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

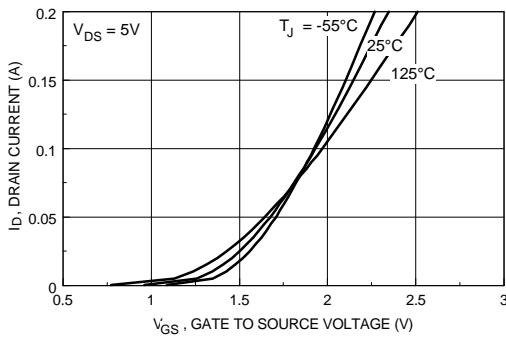


Figure 5. Transfer Characteristics.

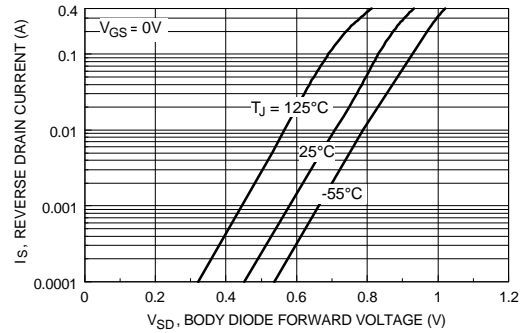


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

## Typical Electrical Characteristics: N-Channel (continued)

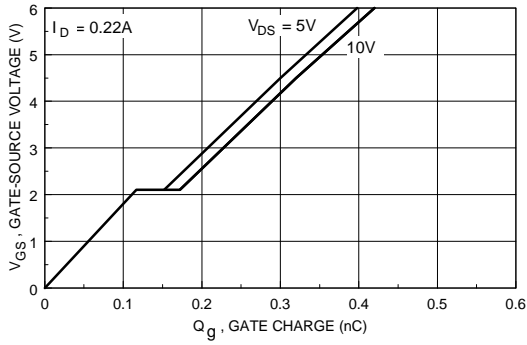


Figure 7. Gate Charge Characteristics.

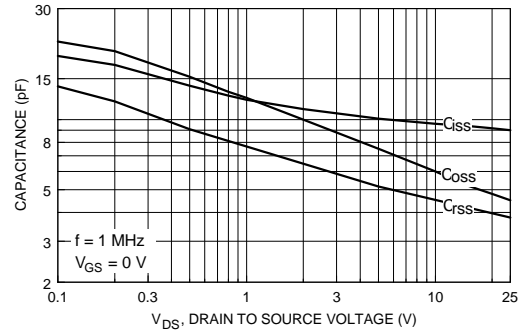


Figure 8. Capacitance Characteristics.

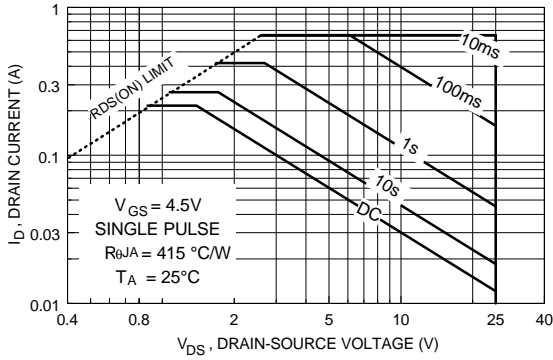


Figure 9. Maximum Safe Operating Area.

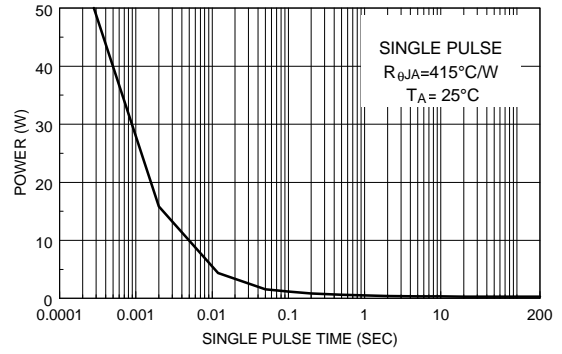


Figure 10. Single Pulse Maximum Power Dissipation.

## Typical Electrical Characteristics: P-Channel

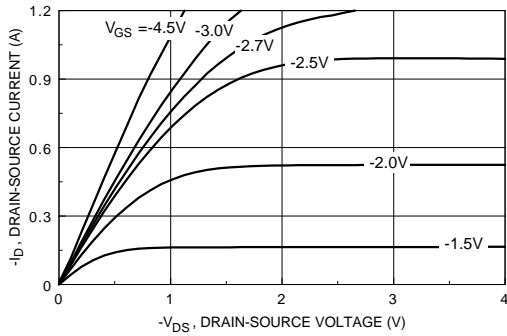


Figure 11. On-Region Characteristics.

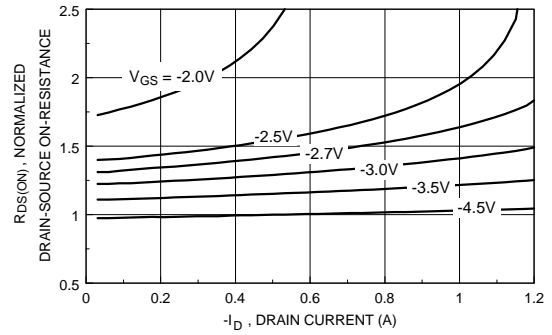


Figure 12. On-Resistance Variation with Drain Current and Gate Voltage.

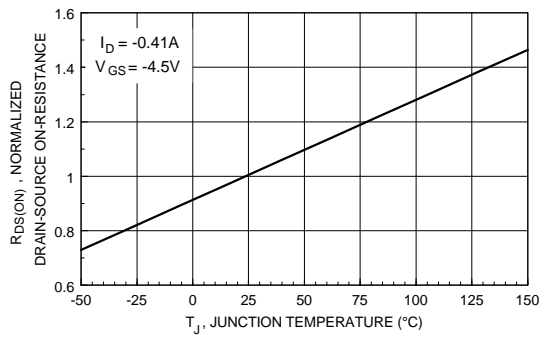


Figure 13. On-Resistance Variation with Temperature.

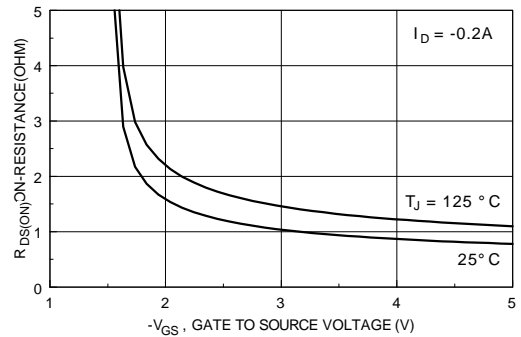


Figure 14. On-Resistance Variation with Gate-to-Source Voltage.

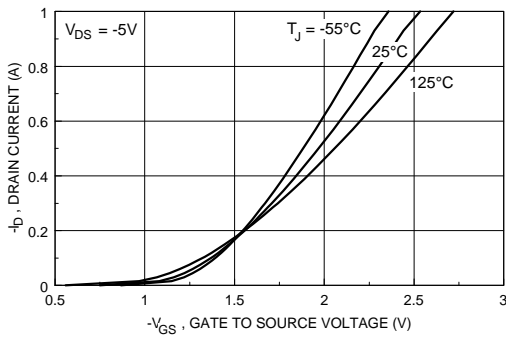


Figure 15. Transfer Characteristics.

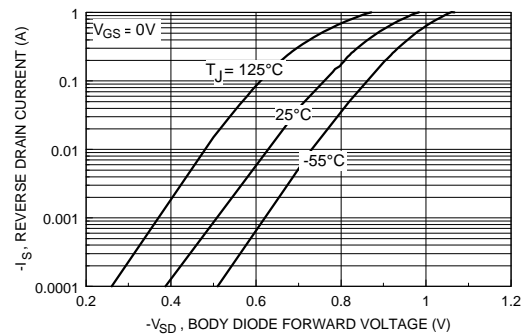
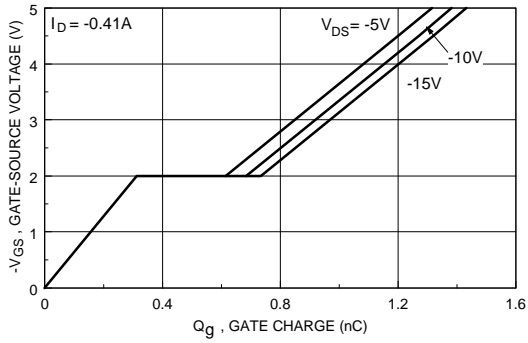
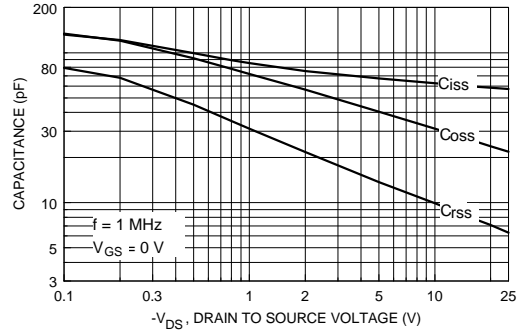


Figure 16. Body Diode Forward Voltage Variation with Source Current and Temperature.

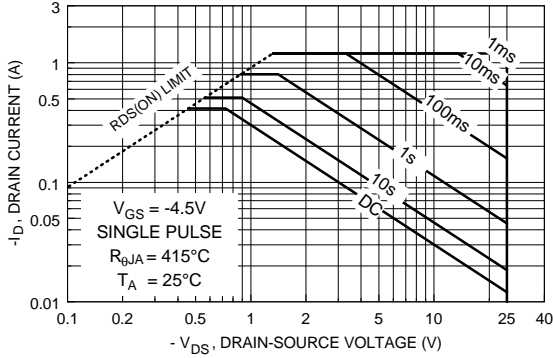
**Typical Electrical Characteristics: P-Channel (continued)**



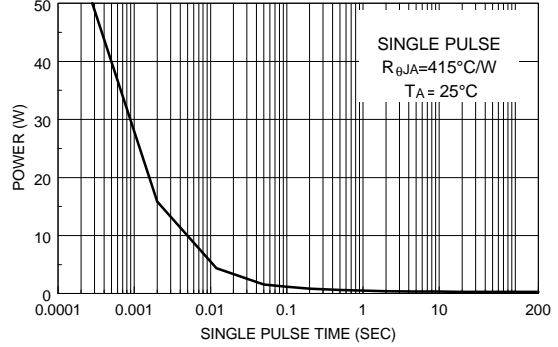
**Figure 17. Gate Charge Characteristics.**



**Figure 18. Capacitance Characteristics.**

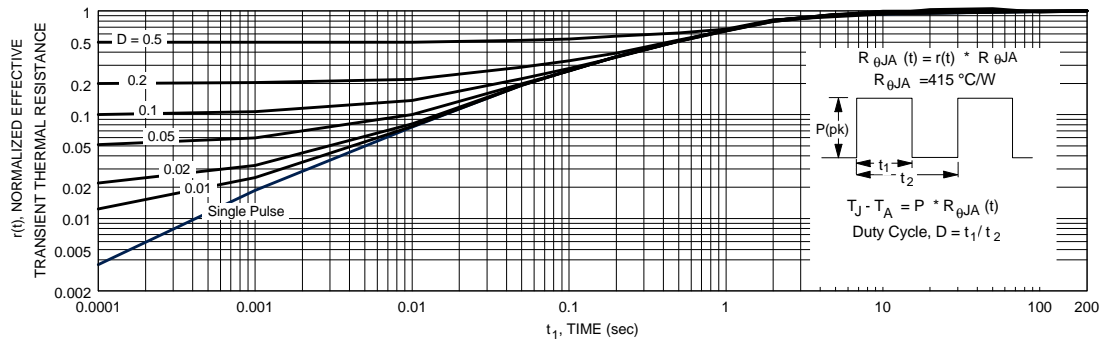


**Figure 19. Maximum Safe Operating Area.**



**Figure 20. Single Pulse Maximum Power Dissipation.**

## Typical Thermal Characteristics: N & P-Channel (continued)



**Figure 21. Transient Thermal Response Curve.**

Thermal characterization performed using the conditions described in note 1.  
 Transient thermal response will change depending on the circuit board design.



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